

# EMP310

UPDATED 05/08/2008

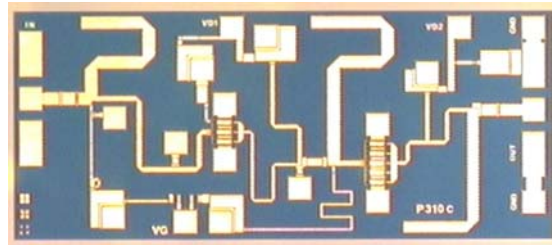
## 21.0 – 24.0 GHz Power Amplifier MMIC

### FEATURES

- 21.0 – 24.0 GHz Operating Frequency Range
- 24.0dBm Output Power at 1dB Compression
- 14.0 dB Typical Small Signal Gain
- -40dBc OIMD3 @Each Tone Pout 14dBm

### APPLICATIONS

- Point-to-point and point-to-multipoint radio
- Military Radar Systems



Dimension: 2250um X 1000um  
Thickness: 75um ± 13um



Caution! ESD sensitive device.

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C, 50 ohm, VDD=7V, IDQ=170mA)

SYMBOL	PARAMETER/TEST CONDITIONS	MIN	TYP	MAX	UNITS
F	Operating Frequency Range	21.0		24.0	GHz
P1dB	Output Power at 1dB Gain Compression	23.0	24.0		dBm
G <sub>ss</sub>	Small Signal Gain	11.0	14.0		dB
OIMD3	Output 3 <sup>rd</sup> Order Intermodulation Distortion @Δf=10MHz, Each Tone Pout 14dBm		-40	-37	dBc
Input RL	Input Return Loss		-10	-8	dB
Output RL	Output Return Loss		-10	-8	dB
I <sub>dss</sub>	Saturate Drain Current V <sub>DS</sub> =3V, V <sub>GS</sub> =0V	211	264	317	mA
V <sub>DD</sub>	Power Supply Voltage		7	8	V
R <sub>th</sub>	Thermal Resistance (Au-Sn Eutectic Attach)		34		°C/W
T <sub>b</sub>	Operating Base Plate Temperature	-35		+85	°C

### ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION<sup>1,2</sup>

SYMBOL	CHARACTERISTIC	VALUE
V <sub>DS</sub>	Drain to Source Voltage	8 V
V <sub>GS</sub>	Gate to Source Voltage	-4 V
I <sub>DD</sub>	Drain Current	I <sub>dss</sub>
I <sub>GSF</sub>	Forward Gate Current	4mA
P <sub>IN</sub>	Input Power	@ 3dB compression
T <sub>CH</sub>	Channel Temperature	150°C
T <sub>STG</sub>	Storage Temperature	-65/150°C
P <sub>T</sub>	Total Power Dissipation	3.4W

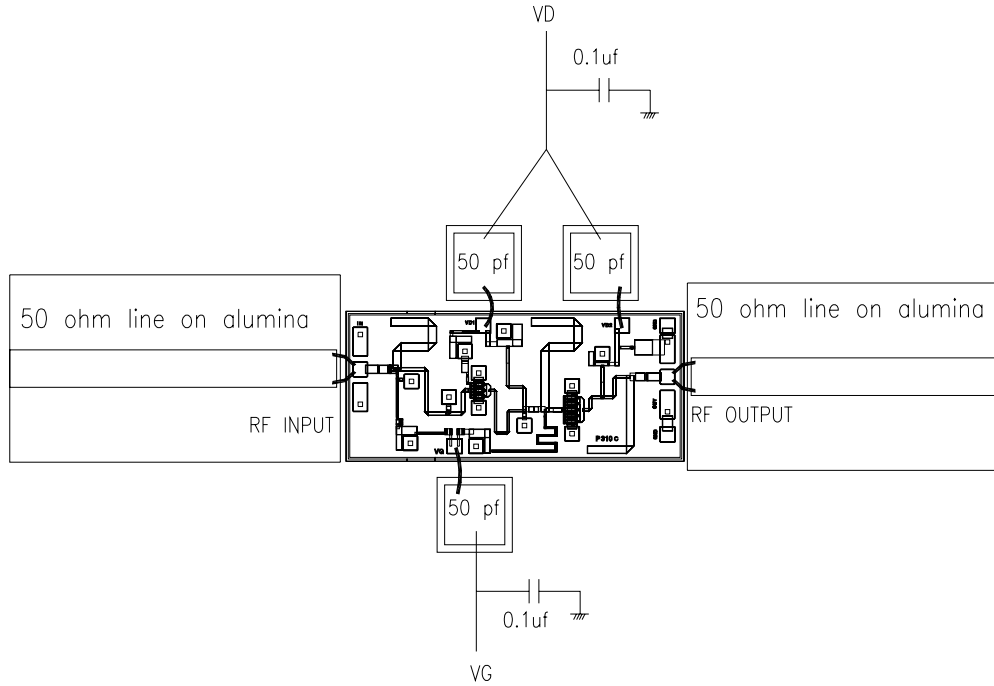
1. Operating the device beyond any of the above rating may result in permanent damage.  
2. Bias conditions must also satisfy the following equation  $V_{DS} * I_{DS} < (T_{CH} - T_{HS}) / R_{TH}$ ; where T<sub>HS</sub> = ambient temperature

# EMP310

UPDATED 05/08/2008

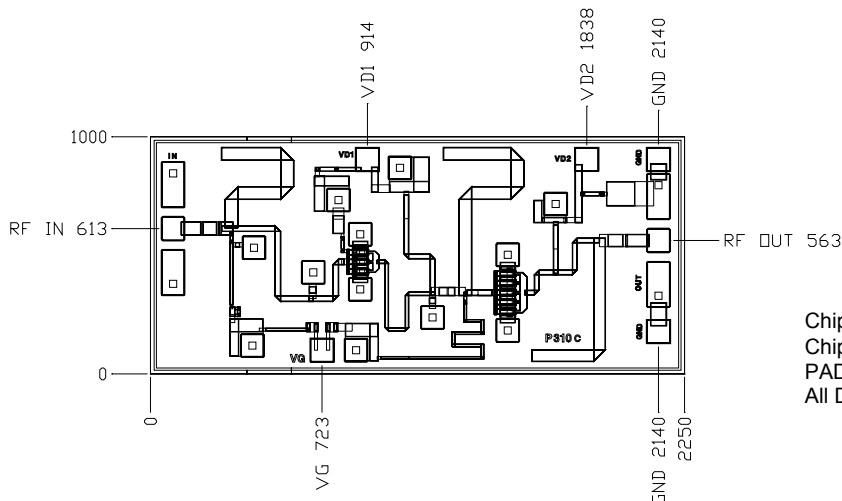
## 21.0 – 24.0 GHz Power Amplifier MMIC

### ASSEMBLY DRAWING



The length of RF wires should be as short as possible. Use at least two wires between RF pad and 50 ohm line and separate the wires to minimize the mutual inductance.

### CHIP OUTLINE



Chip Size 1000 x 2250 microns  
 Chip Thickness: 75 ± 13 microns  
 PAD Dimensions: 100 x 100 microns  
 All Dimensions in Microns

Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085  
 Phone: 408-737-1711 Fax: 408-737-1868 Web: [www.excelics.com](http://www.excelics.com)

page 2 of 3  
 Revised May 2008



# EMP310

UPDATED 05/08/2008

## 21.0 – 24.0 GHz Power Amplifier MMIC

### DISCLAIMER

EXCELICS SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. EXCELICS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN.

### LIFE SUPPORT POLICY

EXCELICS SEMICONDUCTOR PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF EXCELICS SEMICONDUCTOR, INC.

AS HERE IN:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

---

Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085  
Phone: 408-737-1711 Fax: 408-737-1868 Web: [www.excelics.com](http://www.excelics.com)

page 3 of 3  
Revised May 2008